

RF MOS FIELD EFFECT TRANSISTOR

DESCRIPTION:

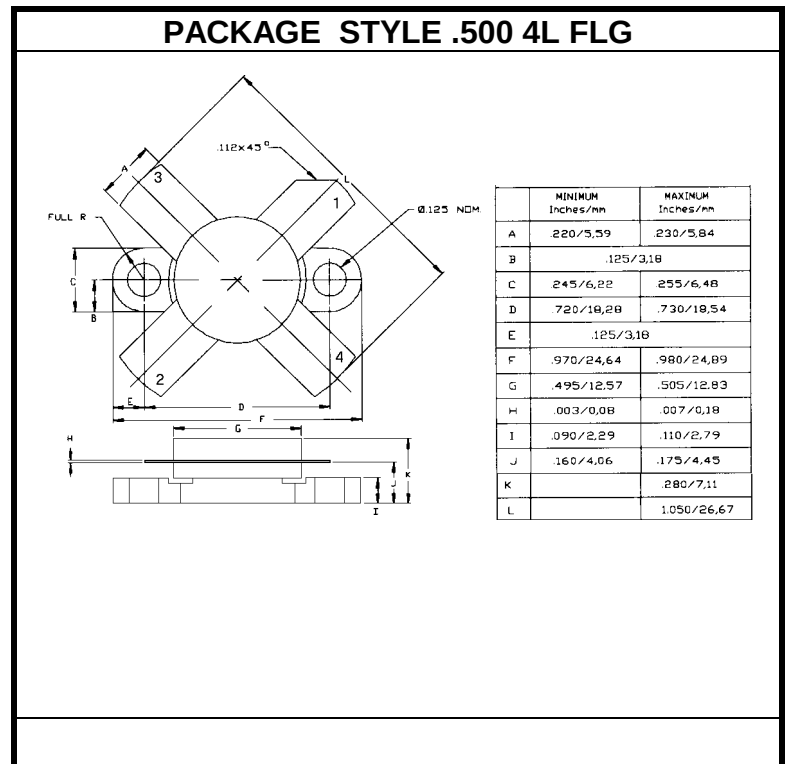
The **SRF4245** is Designed for class AB HF/VHF Applications up to 200 MHz

FEATURES:

- $P_G = 8$ dB at 150 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_D	13.9 A
$V_{(BR)DS}$	125 V
V_{DGR}	125 V
V_{GS}	± 30 V
P_{DISS}	215 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.70 (Typ) $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_D = 100$ mA	125			V
I_{DSS}	$V_{DS} = 50$ V	$V_{GS} = 0$ V			5	mA
I_{GSS}	$V_{GS} = 20$ V	$V_{DS} = 0$ V			1	μA
$V_{FEDS(on)}$	$V_{GS} = 10$ V	$I_D = 10$ A			5	V
G_{FS}	$V_{DS} = 10$ V	$I_D = 5.0$ A	4			mhos
C_{ISS}	$V_{DS} = 50$ V	$V_{GS} = 0$ V			500	pF
C_{OSS}					250	
C_{RSS}					50	
P_{OUT} P_G	$V_{DS} = 50$ V	$I_{DQ} = 250$ mA	150 8			W dB

